



MMBF170

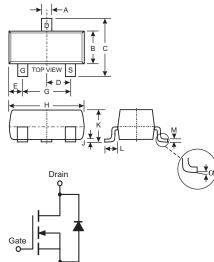
N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead Free/RoHS Compliant (Note 2)

Mechanical Data

- Case: SOT-23
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Marking: (See Page 2) K6Z
- Ordering & Date Code Information: See Page 2
- Weight: 0.008 grams (approximate)



Source

SOT-23								
Dim	Min	Мах						
Α	0.37	0.51						
В	1.20	1.40 2.50 1.03 0.60 2.05 3.00						
С	2.30							
D	0.89							
Е	0.45							
G	1.78							
Н	2.80							
J	0.013	0.10						
К	0.903	1.10						
L	0.45	0.61						
М	0.085	0.180						
α	0°	8°						
All Dir	nensions	in mm						

Maximum Ratings @ T_A = 25°C unless otherwise specified

Characteristic		Symbol	MMBF170	Units	
Drain-Source Voltage		V _{DSS}	60	V	
Drain-Gate Voltage $R_{GS} \leq 1.0 M\Omega$		V _{DGR}	60	V	
Gate-Source Voltage	Continuous Pulsed	V _{GSS}	±20 ±40	V	
Drain Current (Note 1)	Continuous Pulsed	I _D	500 800	mA	
Total Power Dissipation (Note 1)		P _d	300 1.80	mW mW/°C	
Thermal Resistance, Junction to Ambie	ent	R _{θJA}	417	K/W	
Operating and Storage Temperature R	ange	Tj, T _{STG}	-55 to +150	°C	

Note: 1. Device mounted on FR-5 PCB 1.0 x 0.75 x 0.062 inch pad layout as shown on Diodes, Inc. suggested pad layout AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

2. No purposefully added lead.



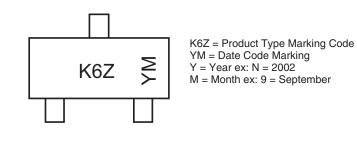
Electrical Characteristics @ T _A	= 25°C unless otherw	vise spec	cified			
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 3)						•
Drain-Source Breakdown Voltage	BV _{DSS}	60	70	_	V	$V_{GS} = 0V, I_D = 100 \mu A$
Zero Gate Voltage Drain Current	I _{DSS}	_		1.0	μA	$V_{DS} = 60V, V_{GS} = 0V$
Gate-Body Leakage	IGSS	_		±10	nA	$V_{GS} = \pm 15V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	0.8	2.1	3.0	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$
Static Drain-Source On-Resistance		_		5.0 5.3	Ω	$V_{GS} = 10V, I_D = 200mA$ $V_{GS} = 4.5V, I_D = 50mA$
Forward Transconductance	g fs	80			mS	$V_{DS} = 10V, I_D = 0.2A$
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{iss}	_	22	40	pF	
Output Capacitance	C _{oss}	_	11	30	pF	V _{DS} = 10V, V _{GS} = 0V f = 1.0MHz
Reverse Transfer Capacitance	C _{rss}	_	2.0	5.0	pF] ••••••
SWITCHING CHARACTERISTICS						
Turn-On Time	t _{on}	_		10	ns	$V_{DD} = 25V, I_D = 0.5A,$
Turn-Off Time	t _{off}	_	_	10	ns	$V_{GS} = 10V, R_{GEN} = 50\Omega$

Notes: 3. Short duration test pulse used to minimize self-heating effect.

Ordering Information (Note 4)									
Device	Packaging	Shipping							
MMBF170-7-F	SOT-23	3000/Tape & Reel							

Notes: 4. For Packaging Details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

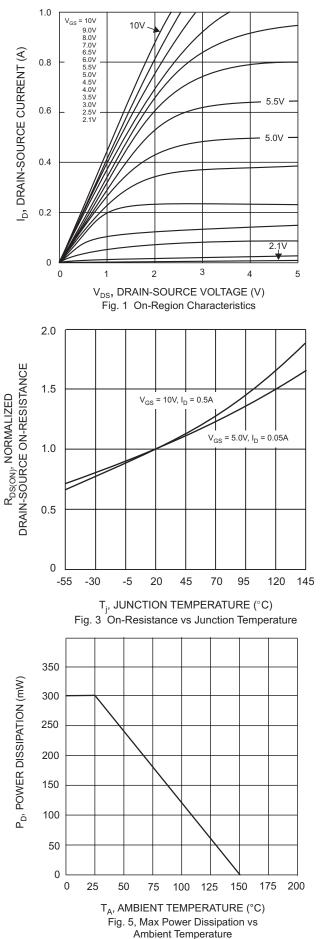
Marking Information

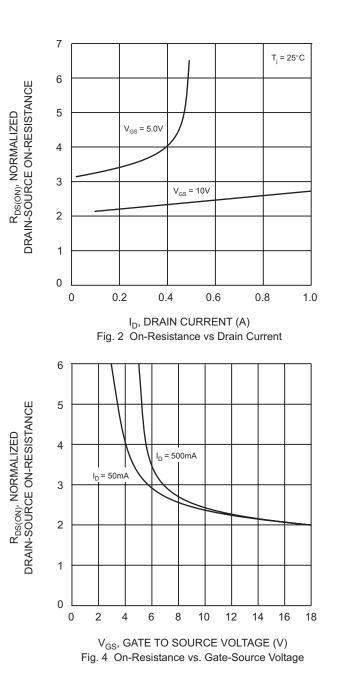


Date Code Key

Year	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009
Code	J	К	L	М	Ν	Р	R	S	Т	U	V	W
Month	Jan	Feb	March	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code		0	2	4	5	6	7	0	0	0	N	D









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